

### BDX34/A/B/C

### **Power Linear and Switching Applications**

- High Gain General Purpose
- Power Darlington TR
- Complement to BDX33/33A/33B/33C respectively



1.Base 2.Collector 3.Emitter

### **PNP Epitaxial Silicon Transistor**

### Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage		
	: BDX34	- 45	V
	: BDX34A	- 60	V
	: BDX34B	- 80	V
	: BDX34C	- 100	V
V <sub>CEO</sub>	Collector-Emitter Voltage		
020	: BDX34	- 45	V
	: BDX34A	- 60	V
	: BDX34B	- 80	V
	: BDX34C	- 100	V
I <sub>C</sub>	Collector Current (DC)	- 10	А
I <sub>CP</sub>	*Collector Current (Pulse)	- 15	А
I <sub>B</sub>	Base Current	- 0.25	А
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> =25°C)	70	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	- 65 ~ 150	°C

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<b>Flectrical</b>	Characteristics T <sub>C</sub> =25°C unless otherwise noted
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Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
V <sub>CEO</sub> (sus)	* Collector-Emitter Sustaining Voltage : BDX34 : BDX34A	I <sub>C</sub> = -100mA, I <sub>B</sub> = 0	- 45 - 60			V
	: BDX34A : BDX34B : BDX34C		- 80 - 80 - 100			V V
V <sub>CER</sub> (sus)	* Collector-Emitter Sustaining Voltage : BDX34 : BDX34A : BDX34B : BDX34C	$I_C = -1 \ 00\text{mA}, I_B = 0$ $R_{BE} = 100\Omega$	- 45 - 60 - 80 - 100			V V V
V <sub>CEV</sub> (sus)	* Collector-Emitter Sustaining Voltage : BDX34 : BDX34A : BDX34B : BDX34C	I <sub>C</sub> = - 100mA, I <sub>B</sub> = 0 V <sub>BE</sub> = - 1.5V	- 45 - 60 - 80 - 100			V V V
I <sub>CBO</sub>	Collector Cut-off Current : BDX34 : BDX34A : BDX34B : BDX34C	V <sub>CB</sub> = - 45V, I <sub>E</sub> = 0 V <sub>CB</sub> = - 60V, I <sub>E</sub> = 0 V <sub>CB</sub> = - 80V, I <sub>E</sub> = 0 V <sub>CB</sub> = - 100V, I <sub>E</sub> = 0			- 0.2 - 0.2 - 0.2 - 0.2	mA mA mA
I <sub>CEO</sub>	Collector Cut-off Current : BDX34 : BDX34A : BDX34B : BDX34C	V <sub>CE</sub> = - 22V, I <sub>B</sub> = 0 V <sub>CE</sub> = - 30V, I <sub>B</sub> = 0 V <sub>CE</sub> = - 40V, I <sub>B</sub> = 0 V <sub>CF</sub> = - 50V, I <sub>B</sub> = 0			- 0.5 - 0.5 - 0.5 - 0.5	mA mA mA
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB} = -5V, I_{C} = 0$			- 5	mA
h <sub>FE</sub>	* DC Current Gain : BDX34/34A : BDX34B/34C	V <sub>CE</sub> = - 3V, I <sub>C</sub> = - 4A V <sub>CE</sub> = - 3V, I <sub>C</sub> = - 3A	750 750			
V <sub>CE</sub> (sat)	* Collector-Emitter Saturation Voltage : BDX34/34A : BDX34B/34C	I <sub>C</sub> = - 4A, I <sub>B</sub> = - 8mA I <sub>C</sub> = - 3A, I <sub>B</sub> = - 6mA			- 2.5 - 2.5	V
V <sub>BE</sub> (on)	* Base-Emitter ON Voltage : BDX34/34A : BDX34B/34C	V <sub>CE</sub> = - 3V, I <sub>C</sub> = - 4A V <sub>CE</sub> = - 3V, I <sub>C</sub> = - 3A			- 2.5 - 2.5	V V
$V_{F}$	* Parallel Diode Forward Voltage	I <sub>F</sub> = - 8A			- 4	V

<sup>\*</sup> Pulse Test: PW=300μs, duty Cycle =1.5% Pulsed

# **Typical Characteristics**

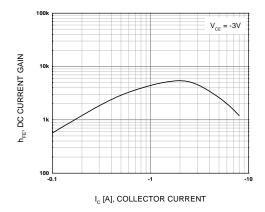


Figure 1. DC Current Gain

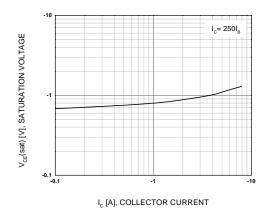


Figure 2. Collector-Emitter Saturation Voltage

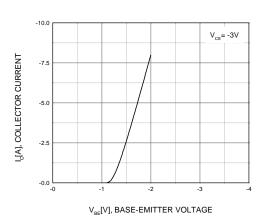


Figure 3. Base-Emitter On Voltage

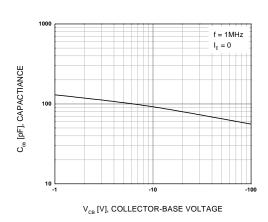


Figure 4. Output Capacitance

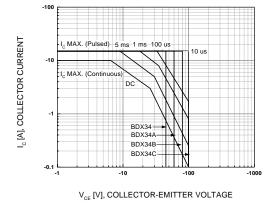


Figure 5. Safe Operating Area

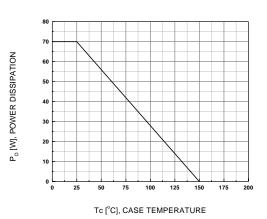
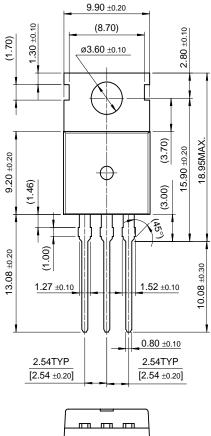


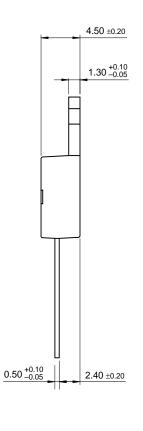
Figure 6. Power Derating

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## **Package Demensions**

## TO-220





10.00 ±0.20

Dimensions in Millimeters

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